



# Recent Development of IBIS and Related EDA Technologies

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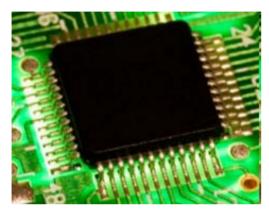


# Agenda

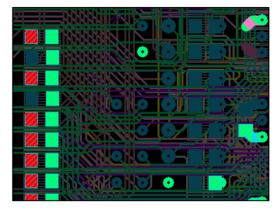
- Review IBIS's role in high-speed SI analysis, especially those new developments, from device modeling, interconnect modeling, and system level simulation automation perspectives.
- Discuss how IBIS as a standard, provides some of the leading technologies for the high-speed design, modeling and simulation industry; whereas in some areas, IBIS standards are lagging behind what industry is doing.
- Promote the thinking of what our current industry needs and what future technologies might bring us.



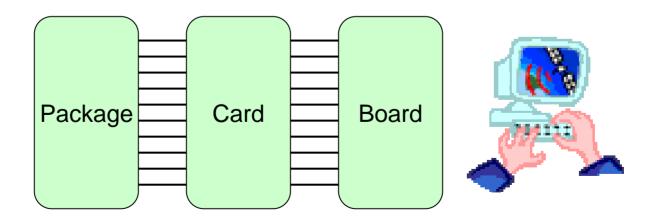
### IBIS's Role in High-Speed SI Analysis



**Device Modeling** 



Interconnect Modeling



System Level Simulation Automation



#### **IBIS Evolution**

#### # ANSI standard **IBIS Development** Multi- Advanced Modeling Interface (AMI) **IBIS 5.0** Gate modulation support Lingual Current distribution support Added analog-only support (Verilog-A) **IBIS 4.2<sup>#</sup>** Fixes for standardization Links to Verilog-AMS, VHDL-AMS **IBIS 4.1** and Berkeley SPICE files Differential thresholds, loads New meas. & delay loads **IBIS 4.0** Golden Waveforms and loads • All IBIS 2.1 features plus Package modeling **IBIS 3.2#** Series devices Scheduled drivers 1990 200. 200 POO

> Reference: New Table-based Keywords in IBIS 5.0, Michael Mirmak, 2008 IBIS Summit China



# **IBIS Latest Status in 2009**

- Device modeling enhancement
  - BIRDs for IBIS 5.0
    - BIRD74.6 EMI Parameters
    - BIRD95.6 Power Integrity Analysis using IBIS
    - BIRD97.2/98.1 Gate Modulation Effect
    - BIRD103.1 [Model Spec] DDR2 Over/Undershoot
    - BIRD104.1 Algorithmic Modeling API
    - BIRD107.2 Update to Algorithmic Modeling API
    - BIRD108 Fixing Algorithmic Modeling API Impulse Matrix Nomenclature
- Interconnect modeling enhancement
  - Touchstone 2.0 completed and released
    - Sparse matrices and node-port matching now under development
    - Parser development about to begin

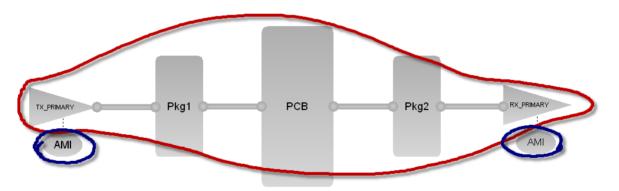


# **IBIS Device Modeling - AMI Development**



## **IBIS AMI Device Model Key Concepts**

- Device models for high-speed channel simulations that need sophisticated FFE and DFE algorithms
  - The Tx –to– Rx pathway is composed of 3 separate entities Tx algorithmic part, Analog channel, Rx algorithmic part



- Model delivered as a dynamically linked library (DLL)
  - Executable models contain and conceal IC company's advanced device algorithms



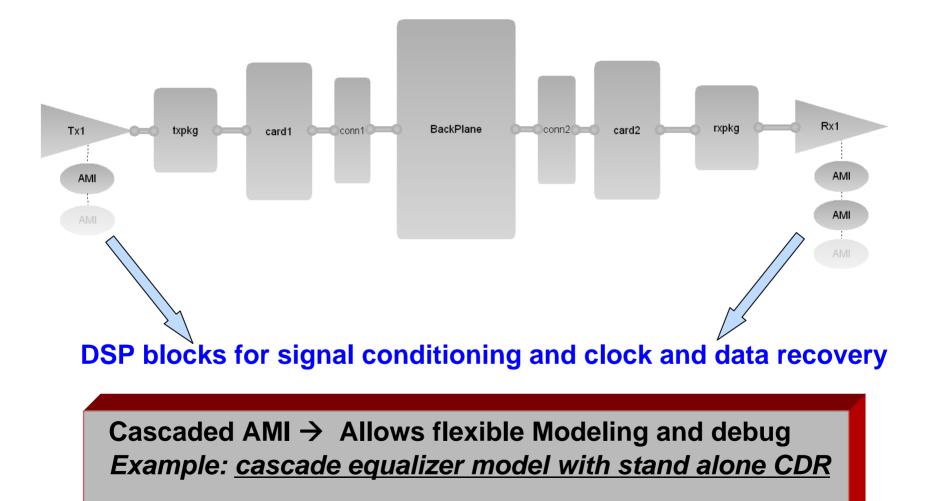


#### **Observations**

- IBIS AMI, a novel idea and technical approach that meets current and future modeling and simulation needs, and also fits the business model for IC company (who provides) and system company (who uses)
- IC technology advances fast, which requires more advanced IBIS AMI models beyond current standard to support existing designs
- The provided IBIS AMI models from some IC Companies are just part of the product line, not complete
- Many IC companies are yet to have the practice or know-how to deliver IBIS AMI models



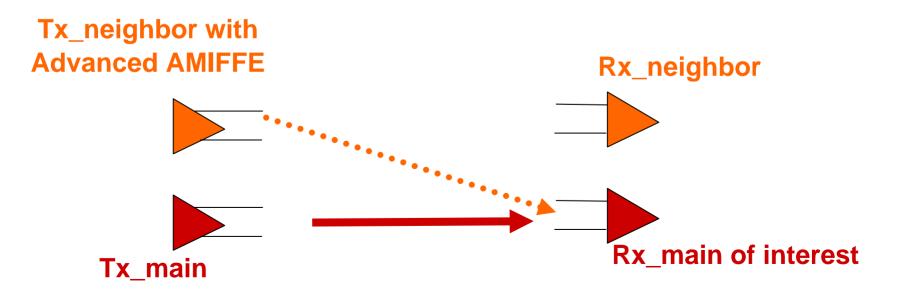
#### Advanced feature needed - Cascaded AMI





### Advanced feature needed: Xtalk aware

- Standard IBIS AMI models are only required to filter the main channel
- Advanced AMIFFE models will optimize the filter coefficients for the main channel, and has the capability to filter the xtalk channel using those coefficients

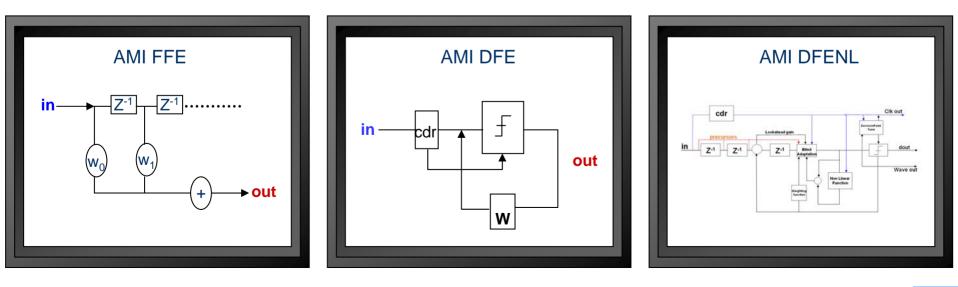




# **Advanced IBIS AMI Function Blocks**

Advanced AMI implementations with highly customizable configurations can model the real world devices

- AMI CDR2 Stand alone clock data recovery
- AMI FFE Feed forward filter model (tap optimization)
- AMI CTF Analog filter model
- AMI DFE DFE with blind adaption
- AMI DFENL DFE with look ahead equalizer



### Beyond IBIS AMI - Hybrid Model Support

•IBIS-AMI

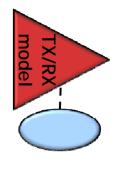
•IBIS with driver schedule

•HSPICE/Encrypted HSPICE

•Verilog-A

•IC companies' proprietary models (C or Matlab based), such as those in IBM HSSCDR

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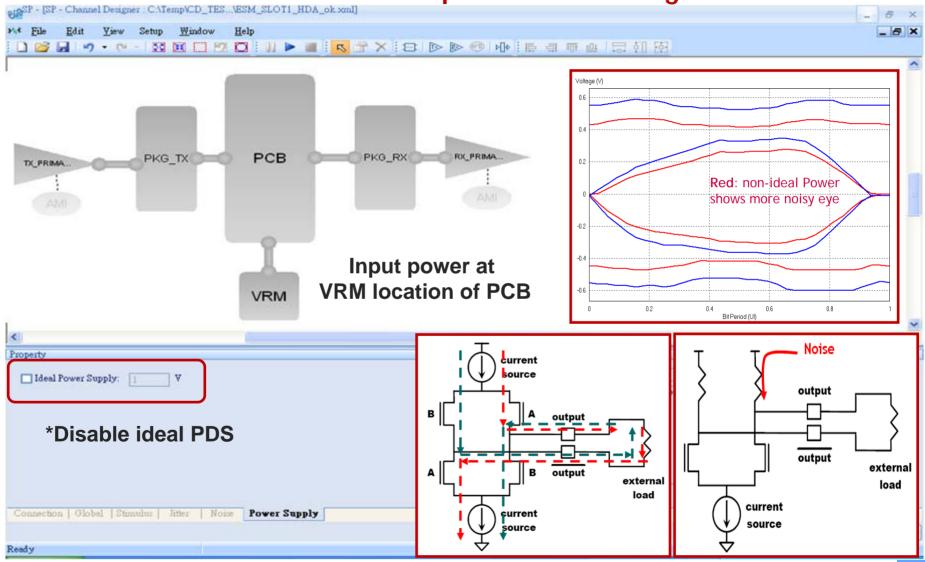


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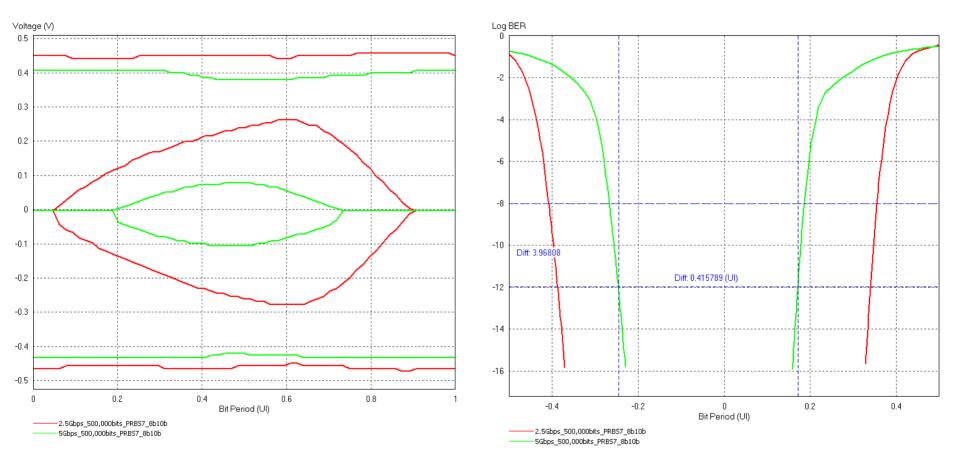


#### Beyond IBIS AMI – Non-Ideal PDS SI Analysis AMI models can be powered through real PDS





# High-speed Gigabit Serial Simulation with AMI models (2.5Gbps Vs 5Gbps)

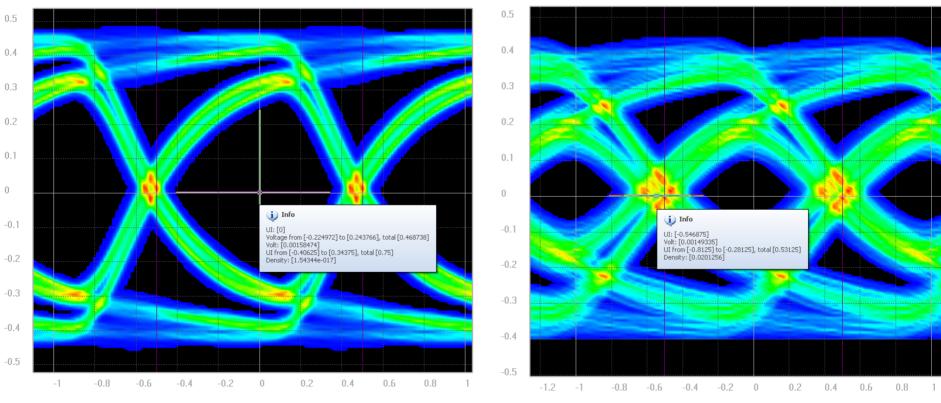


Eye Contour

Bathtub



#### High-speed Gigabit Serial Simulation with AMI models (2.5Gbps Vs 5Gbps)



2.5Gbps Eye Diagram

#### 5Gbps Eye Diagram



# **IBIS Interconnect Modeling - S Parameters**



#### Package RLC models, EBD and S Parameters

- IBIS PKG (IC Package Model) RLC (per pin matrix) is OK for electrical short structures such as IC packages and the frequency response is needed within a few GHz. see reference paper at IBIS Shanghai 2006 <u>http://www.vhdl.org/pub/ibis/summits/oct06a/chitwood.pdf</u>
- IBIS EBD (Electrical Board Description) is designed for electrical long structures but the lack of coupling and return path descriptions makes it unsuitable for high-speed SI see reference paper at IBIS Shanghai 2008 <u>http://www.vhdl.org/pub/ibis/summits/nov08a/xu.pdf</u>

#### • S-Parameter

widely used for accurate high frequency simulation, though has its own issues, is the most popular for interconnect model see reference paper at IBIS Shanghai 2008 <u>http://www.vhdl.org/pub/ibis/summits/nov08a/huang.pdf</u>



# **IBIS Touchstone ver2.0 for S-Parameters**

• Complete backward compatibility with Touchstone 1.0, released in July 2009.

• Mixed-mode support (single ended + diff. signals), which enables SI analysis with the impact of the PDS

• Per-port impedance references. This facilitates power to signal port modeling of coupling and Power Integrity simulation.

• Removal of upper limits on number of data points and number of ports. This facilitates modeling of large ICs.

• Some minor fixes and clarifications. In Touchstone 1.0, Z and Y were normalized with respect to Z0. In Touchstone 2.0, Z and Y are non-normalized and independent of Z0.

Reference: <u>http://www.semiconductorsimulation.com/IBIS%20Committee.pdf</u>





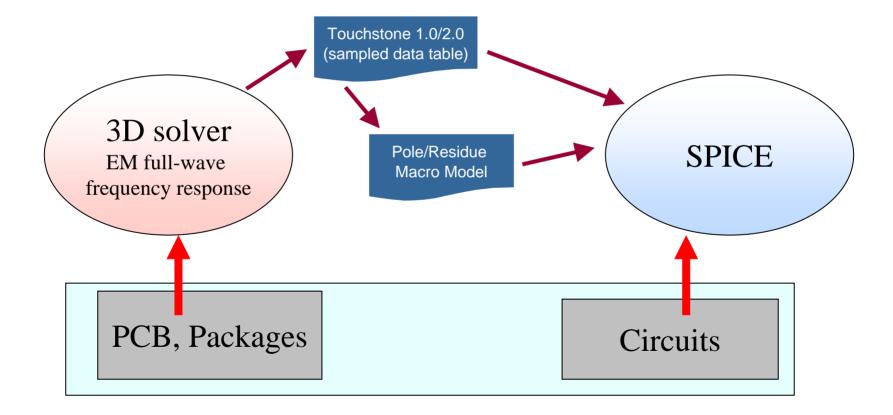
### Beyond Touchstone 2.0

- For a large S matrix (model for many signal and/or power/ground nets), the Touchstone data file could be huge (few hundreds of MB)
- New format under IBIS task team investigation Pole/Zero format
  - Extreme compact, only store poles and residues for the rational function approximation
  - Highly efficient simulation, using recursive convolution
  - S-parameter data are stored as vector fitted curve so it is an approximation
- Proprietary format Sigrity BNP API for S-parameter
  - Very Compact and extremely accurate
  - Do not store tabulated data, provides raw data on demand



#### **Current Simulation Flow**

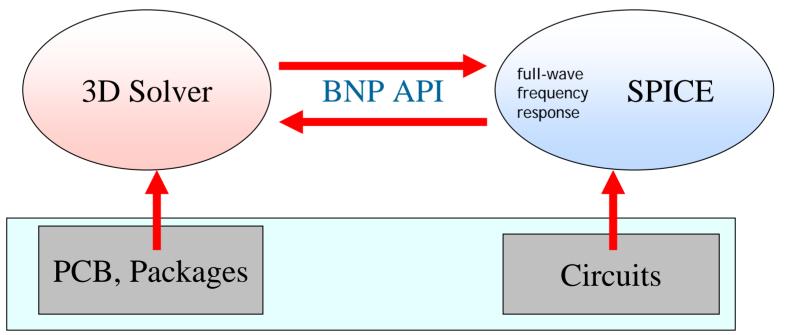
#### Through TouchStone (TS) S-parameter file



#### **SIGRITY**

# **Proprietary Flow for Enhanced Integration**

- Frequency domain data exchange through API with broadband response
  - BNP data file does *not* store the frequency data points as does in a Touchstone file. It calculates any requested frequency point whenever the API is called within the simulation band. Therefore, the need to interpolate S-parameter tabulated data is completely eliminated. Since the API transports raw data, no pole/zero approximation needed.







### S-Parameter Usage Example

Using S-Parameter in both TouchStone and BNP formats in HSPICE

.model Smodel\_name S TSTONEfile=file or BNPfile=file

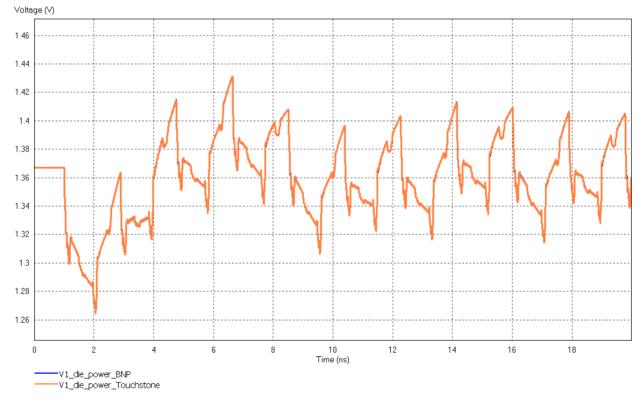
TS file: xyz.snp BNP file: xyz.bnp

BNP file is much smaller than TS file, but yields higher simulation accuracy and convergence

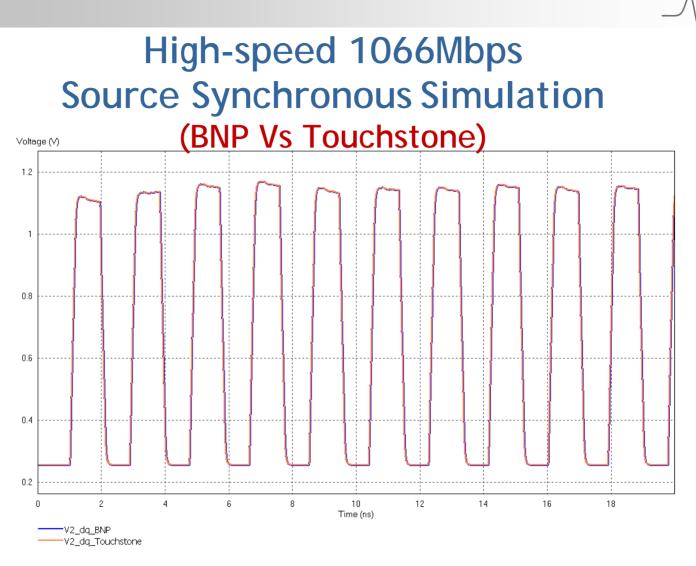
Test Case	Freq #	Touchstone File	Touchstone File Zipped	BNP File
psi_pkg_wb_pre-layout.spd (example folder)	646	1,388 KB	406 KB	24 KB
mixed_extraction.spd (advanced training)	886	10,211 KB	2,771 KB	62 KB
mixed_extraction.spd (all nets enabled)	886	311,105 KB	116,306 KB	1,920 KB

#### SIGRITY

#### High-speed 1066Mbps Source Synchronous Simulation (BNP Vs Touchstone)



- VCC Power @ Die waveform with BNP Vs Touchstone model
- BNP model simulation has higher efficiency, better convergence and accuracy



- DQ @ Board waveform with BNP Vs Touchstone model
- BNP model simulation has higher efficiency, better convergence and accuracy

SIGRIT





#### Summary

- Reviewed IBIS device model AMI and its support
- Reviewed S-parameter as the interconnect model, introduced IBIS Touchstone 2.0 and Sigrity BNP
- Next review will be on how device models and interconnect models are connected for system level simulation automation.





#### Thank You!

